



Substrate Netlist Extraction in Analog Design

With PNAware and PNAwareRC

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Setting the benchmark in Design Support

Through our **comprehensive design and prototyping support**, we enable first-time-right designs not only for digital, but also for **analog mixed-signal designs**.

- > **Feature-rich, proven design kits:** The solid basis for your designs with full access to all process features
- > **Support for multiple EDA vendors:** Choose the flow which fits best to your needs
- > **Largest foundry IP offering:** Reduce design risk and improve time-to-market
- > **Unique X-FAB tools** to solve design challenges, accelerate the design process and enable first-time-right design
- > **Expert support** when needed, from idea to design, tape-out, prototyping and production

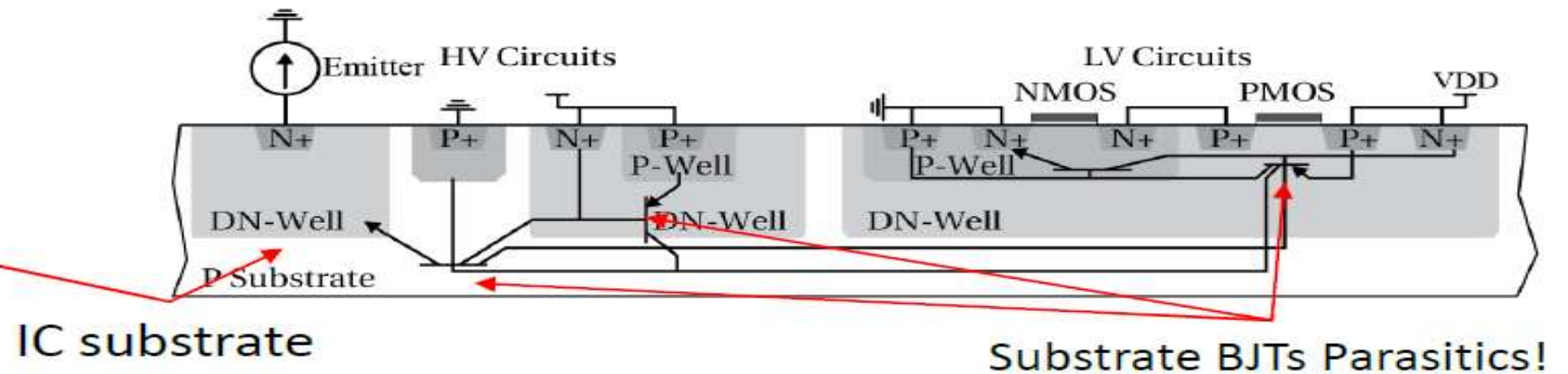
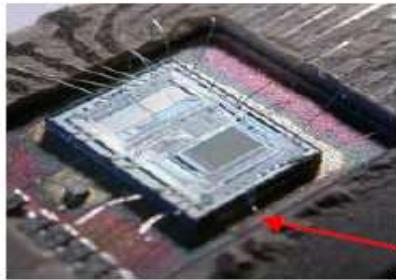


PNAware XSUB

parasitic substrate netlist extraction tool for HV-CMOS

Motivation: Re-designs due to substrate coupling

- A Re-design root cause in Smart Power ICs, like motor drivers
 - some customers are affected by Re-designs due to unwanted substrate coupling
 - today these problems are handled by hand, Trial & Error by very experienced designers after measured silicon: time consuming!
 - Substrate coupling is an active and distributed large signal problem
 - not locally concentrated
 - AC simplifications do not work

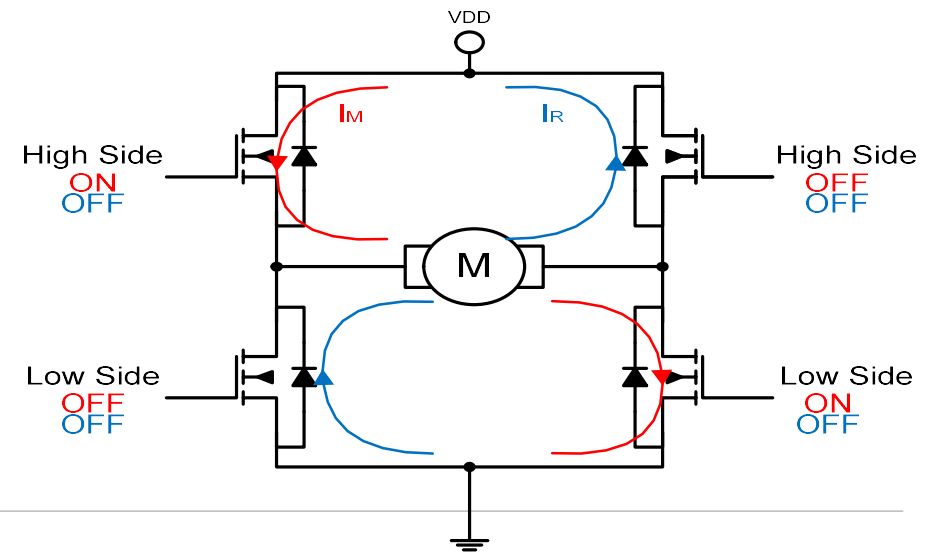


Motivation: Re-designs due to substrate coupling (2)

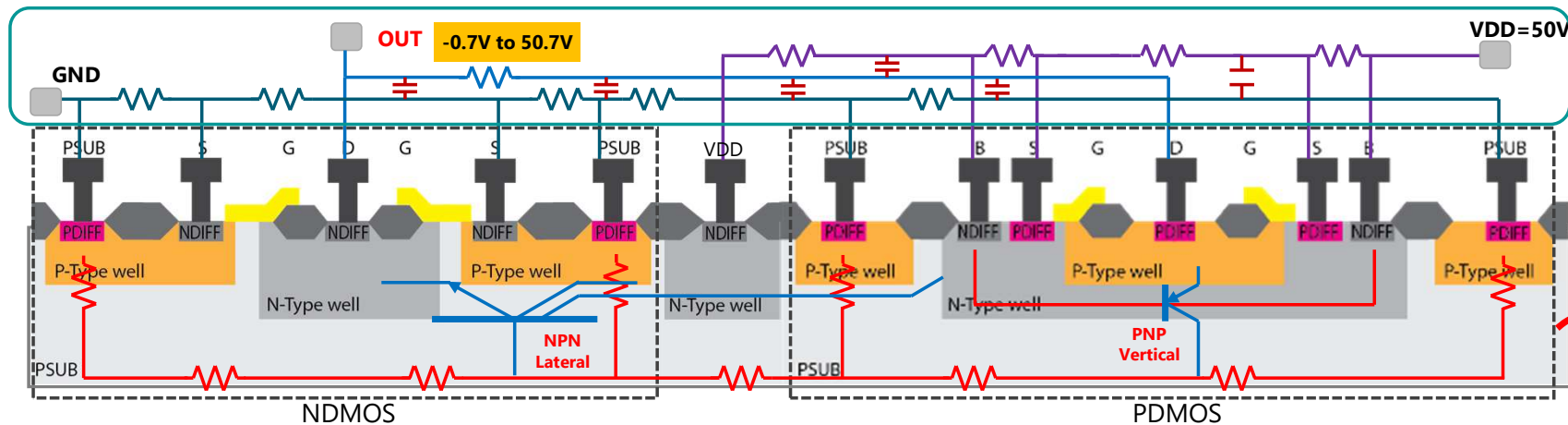
- > EMC, e.g. DPI Tests (=Direct Power Injection, $P \leq 36\text{dBm} = 4\text{W}$)
 - significant portion of DPI problems is accounted to substrate coupling in HV-CMOS

- > Motor driver guardringing concept insufficient
 - Most critical situation: Drain below ground (after LS transistor switched off)
 - Minority carriers (Electrons) can travel several mm in the substrate to any N-type Well
 - Severe disturbance of sensitive circuits
like Bandgaps, ADCs, Pre-drivers...

- > Such Re-designs are expensive
full mask re-designs



Parasitic Elements in HV-CMOS processes

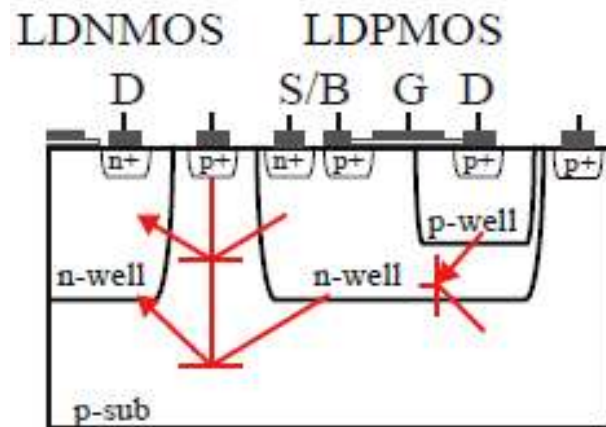


- Metal interconnect and substrate diodes extraction for noise coupling simulations
- Lateral NPN and vertical PNP bipolar transistors. If activated, they generate substrate currents!
- Challenges in control, design and causes failures!

A solution exists

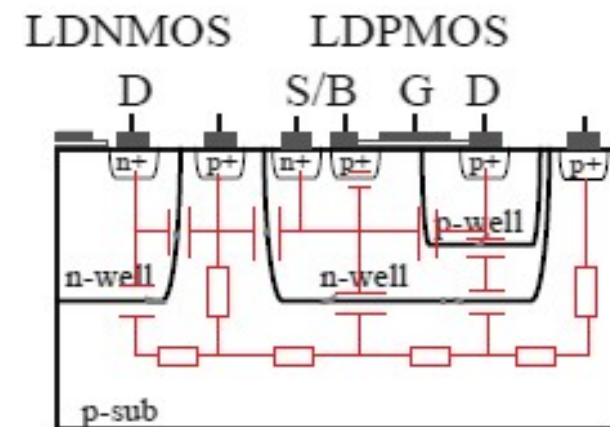
PNAware

Extraction of **substrate lateral bipolar transistors** in with junction-isolated technologies

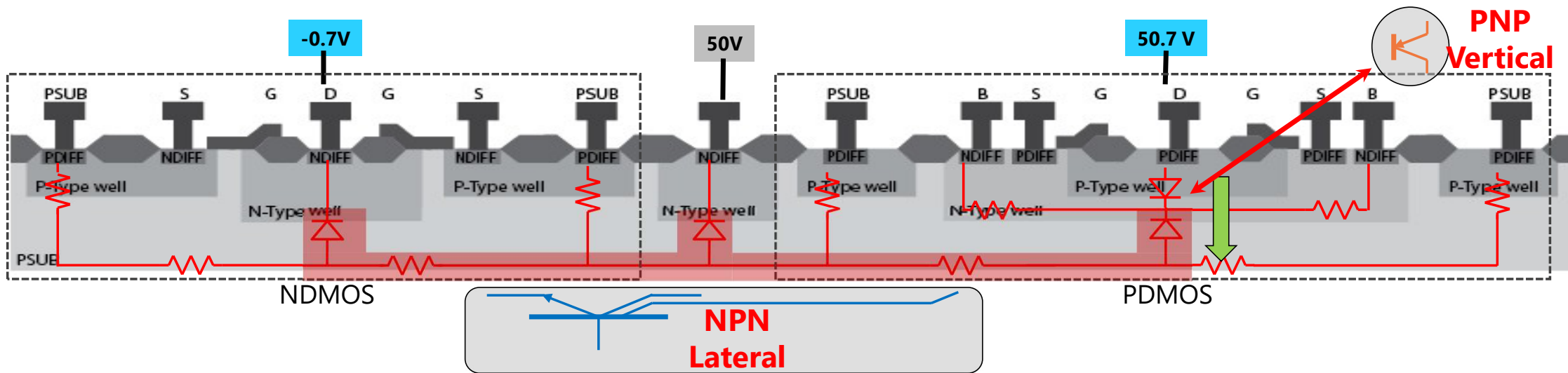


PNAwareRC

Extraction of **substrate passive RC network**



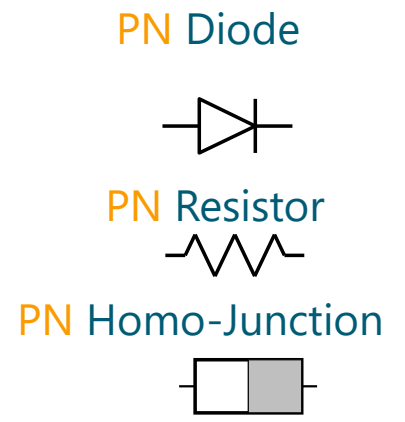
PNAware - Substrate Model Approach



Substrate Model is based on:

- a) Detection of parasitic **pn-junctions** in substrate
- b) Description of parasitic current **propagation** in the substrate
- c) Description of **doping discontinuities** at p-p+ or n-n+ substrate contacts

Parasitic bipolar transistors are **automatically** detected from layout

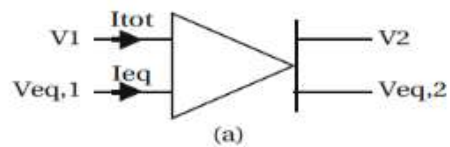


PNAware - 3D Substrate Model

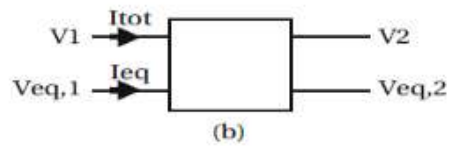
Introduction of three devices with four terminals:

- > top terminals carry substrate voltages and currents
- > bottom terminals carry equivalent voltages and currents which are proportional to excess minority carrier concentration and their gradient.

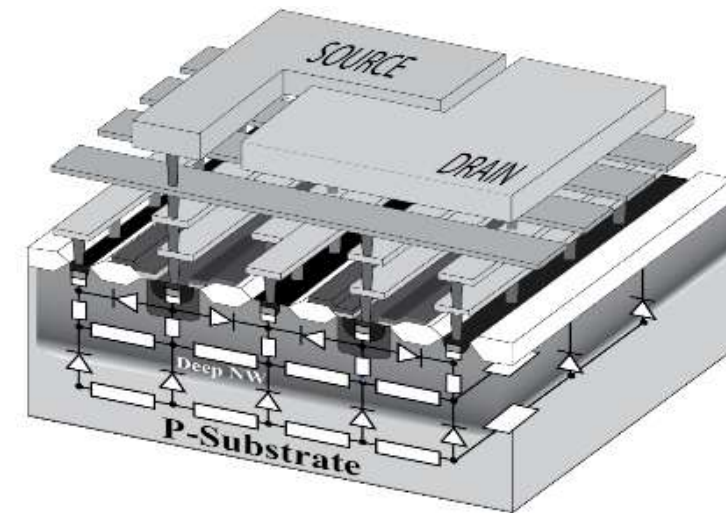
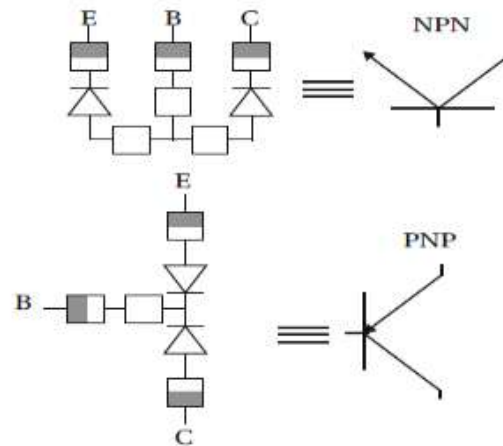
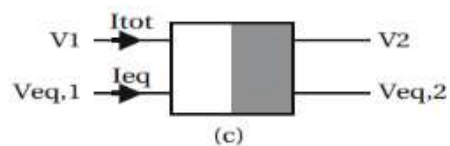
PN Diode



PN Resistor



PN Homo-Junction



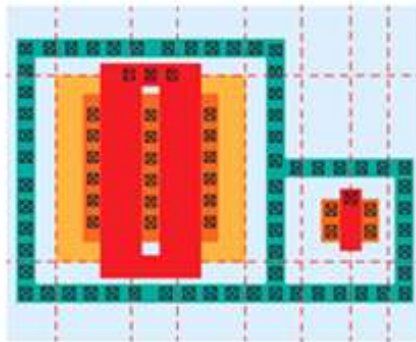
C. Stefanucci, P. Buccella, M. Kayal, J.M. Sallese, Spice-compatible modeling of high injection and propagation of minority carriers in the substrate of Smart Power ICs, *Solid-State Electronics* 105, 2015.

PNAware Operation

Core + Extractor + Model

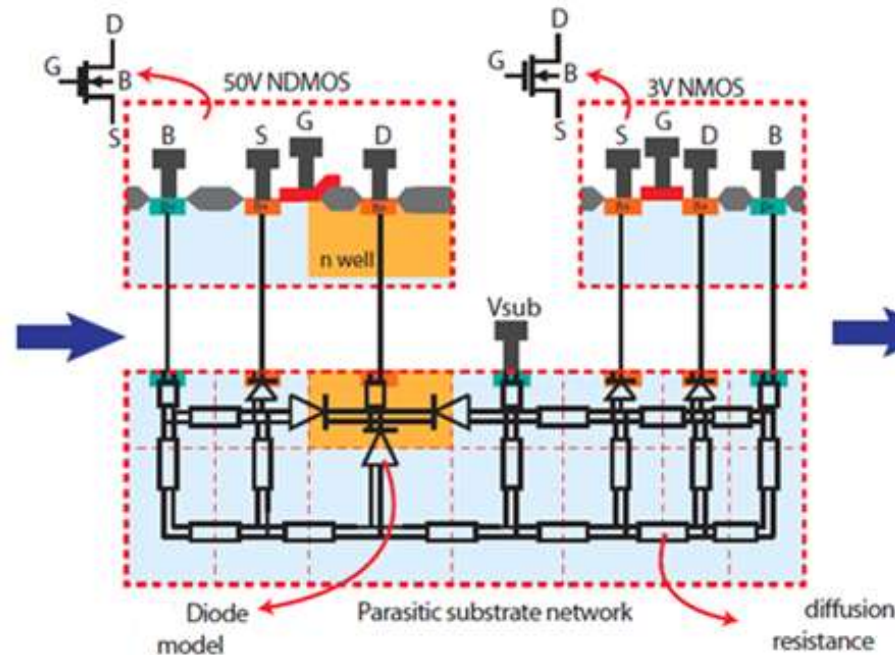
1. MESHING CORE

LAYOUT ANALYSIS
AND MESHING



2. EXTRACTOR

SUBSTRATE EXTRACTION



3. MODEL CARD

POST-LAYOUT
NETLIST SIMULATION



PNAware XSUB: How to use it?

- > To run PNAware: 1. LVS clean design. 2. Add recognition layer SUBEXT in layout over regions of interest

GUI

Substrate Netlist

```

10 subckt xp018_pntc1_block1_ID14_sub
11 + pad(16\ )
12 + pad(6\ )
13 + pad(7\ )
14 //LAYER 0 z
15 XPNhom0 (pad\ (16\ ) pn1_0 0 pnm1_0) hom_pppw_v A=2.370493e-10 Lr1=2.000000e-07 Lr2=6.500000e-07 dm1=2 dm2=6
16 XPNhom1 (pad\ (16\ ) pn2_0 0 pnm2_0) hom_pppw_v A=3.035874e-11 Lr1=2.000000e-07 Lr2=6.500000e-07 dm1=2 dm2=6
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20 XPNhom5 (pad\ (16\ ) pn13_0 0 pnm13_0) hom_pppw_v A=1.122400e-10 Lr1=2.000000e-07 Lr2=6.500000e-07 dm1=2 dm2=6
21 XPNhom6 (pad\ (16\ ) pn14_0 0 pnm14_0) hom_pppw_v A=1.122400e-10 Lr1=2.000000e-07 Lr2=6.500000e-07 dm1=2 dm2=6
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23 XPNhom8 (pad\ (16\ ) pn16_0 0 pnm16_0) hom_pppw_v A=7.410480e-12 Lr1=2.000000e-07 Lr2=6.500000e-07 dm1=2 dm2=6
  
```

Simulation

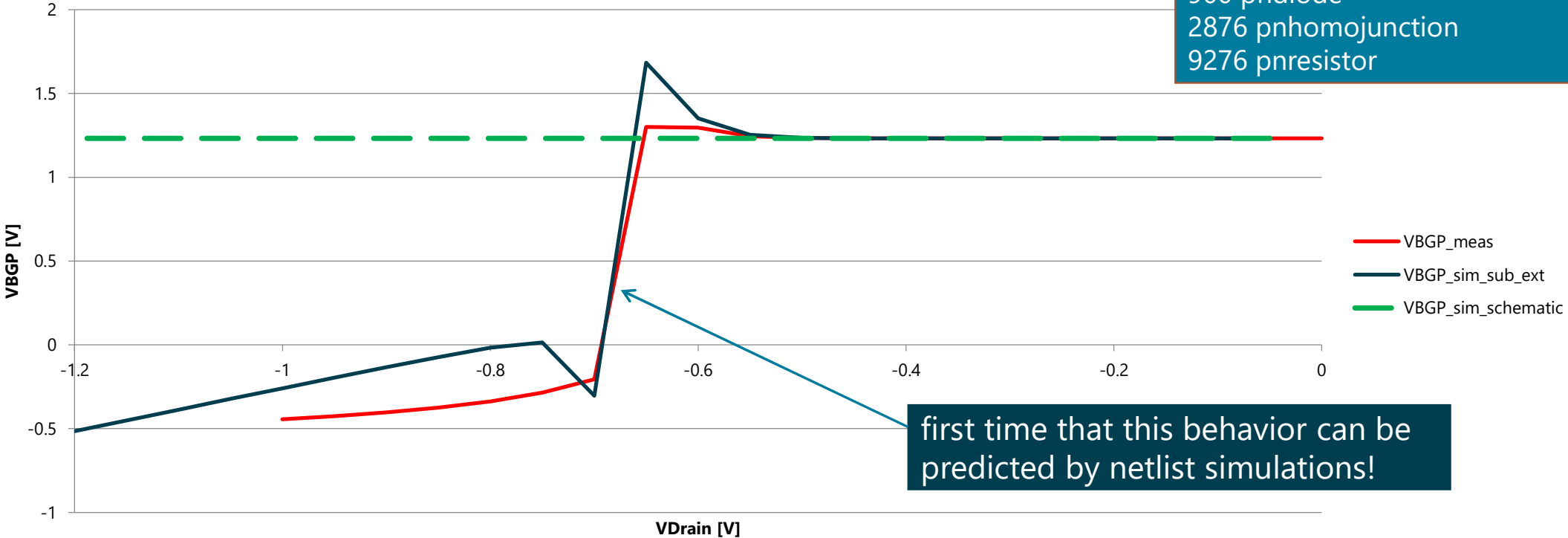
Library	Cell	View Found	View To Use	Inherited View List
PRIMLIB	ddnw60	spectre		spectre_cmos_sch cm...
PRIMLIB	nedd	spectre		spectre_cmos_sch cm...
SUB_MOD_OCT_2018_...	xp018_pntc1_block1_...	sub_extracted_1	sub_extracted_1	spectre_cmos_sch cm...
SUB_MOD_OCT_2018_...	xp018_pntc1_block1_...	schematic		spectre_cmos_sch cm...
analogLib	idc	spectre		spectre_cmos_sch cm...
analogLib	res	spectre		spectre_cmos_sch cm...
analogLib	vdc	spectre		spectre_cmos_sch cm...

Electron Injection test with LDMOS transistor + Bandgap

Drain of NDMOS is pulled below substrate potential and injects electrons
-> no N-type-Well guarding around the LDMOS
-> electrons collected in Bandgap at all NWell connections (pmos, resistors, bipolars)

VBGP – bandgap output voltage

extracted substrate netlist:
900 pndiode
2876 pnhomojunction
9276 pnresistor



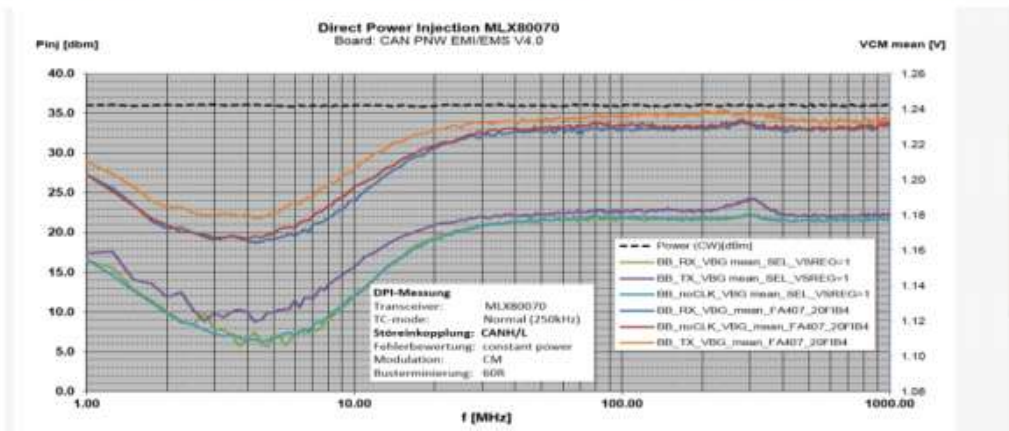
PNAware RC

parasitic substrate netlist extraction tool for SOI

motivation: Re-designs due to substrate coupling

- Re-design root cause in automotive ICs , like CAN-FD-TRX: parasitic Substrate Couplings
 - Even very experienced customers are affected by Re-designs due to unwanted substrate coupling
 - today these problems are handled by hand, Trial & Error by very experienced designers after measured silicon: time consuming!
 - Substrate coupling in Bulk-CMOS is in most cases a distributed multi-collector lateral bipolar problem
 - Substrate coupling in SOI is in most cases a passive RC coupling problem

Measurement results under DPI stress on CANL/H



PNAwareXSUB for substrate netlist extraction in HV-Bulk CMOS

PNAwareRC for substrate netlist extraction in SOI.

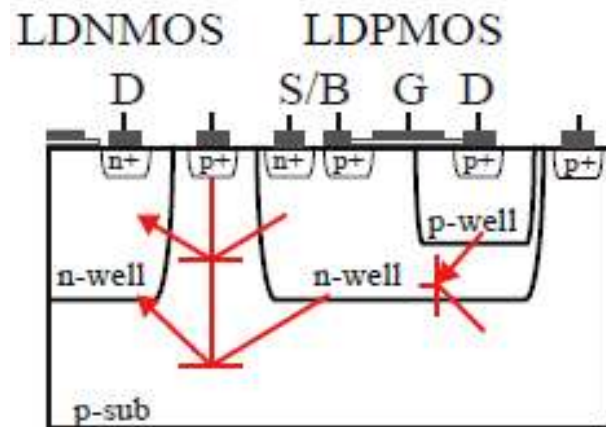
Picture taken from Technology Conference 2022, Dirk Nuernbergk

Dip of the bandgap voltage (VBG and VBG_TC) at low frequencies in between 1 .. 20MHz

A solution exists

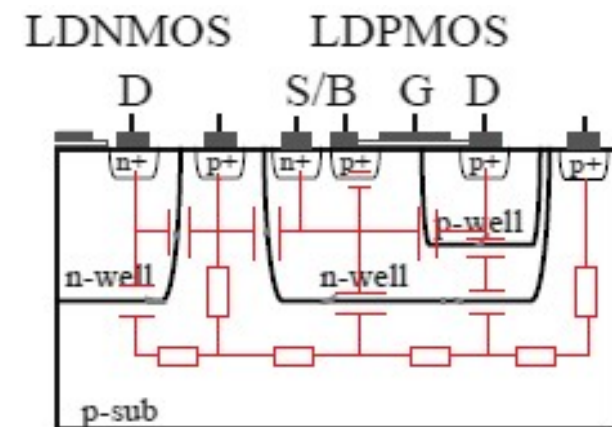
PNAware

Extraction of **substrate lateral bipolar transistors** in with junction-isolated technologies



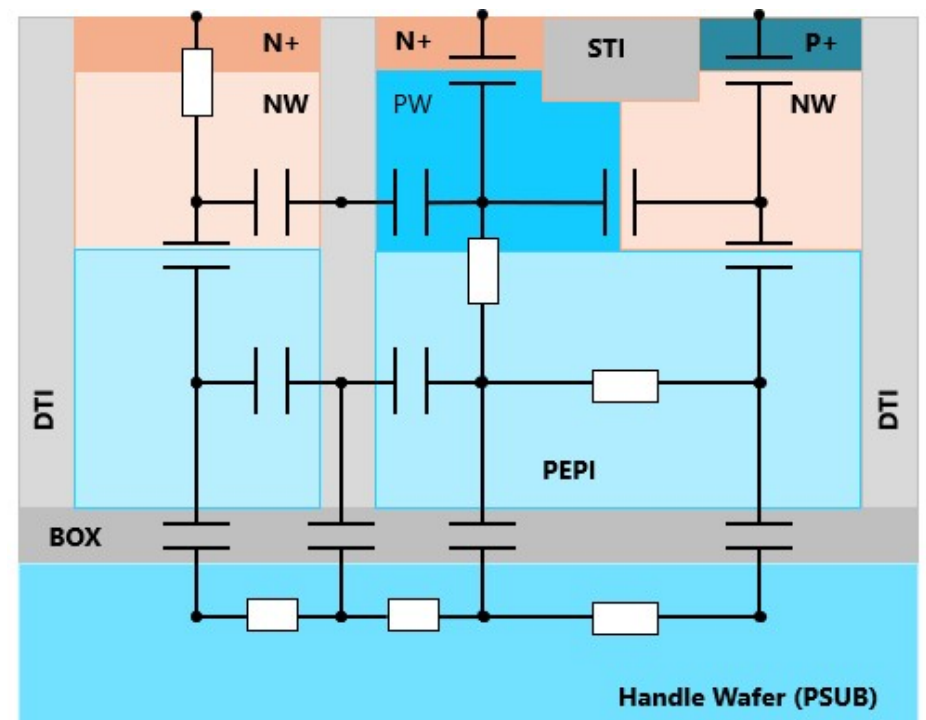
PNAwareRC

Extraction of **substrate passive RC network**



PNAwareRC: SOI process

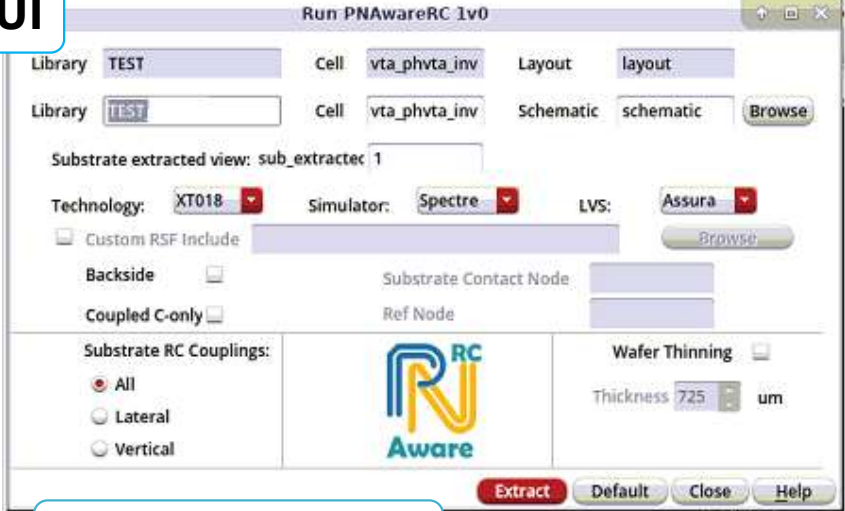
- Even in SOI technologies, the isolation is not perfect, as passive R and C couplings are still present
- In SOI, PNAwareRC extracts a passive RC network including lateral and vertical coupling paths resulting from DTI and BOX isolations



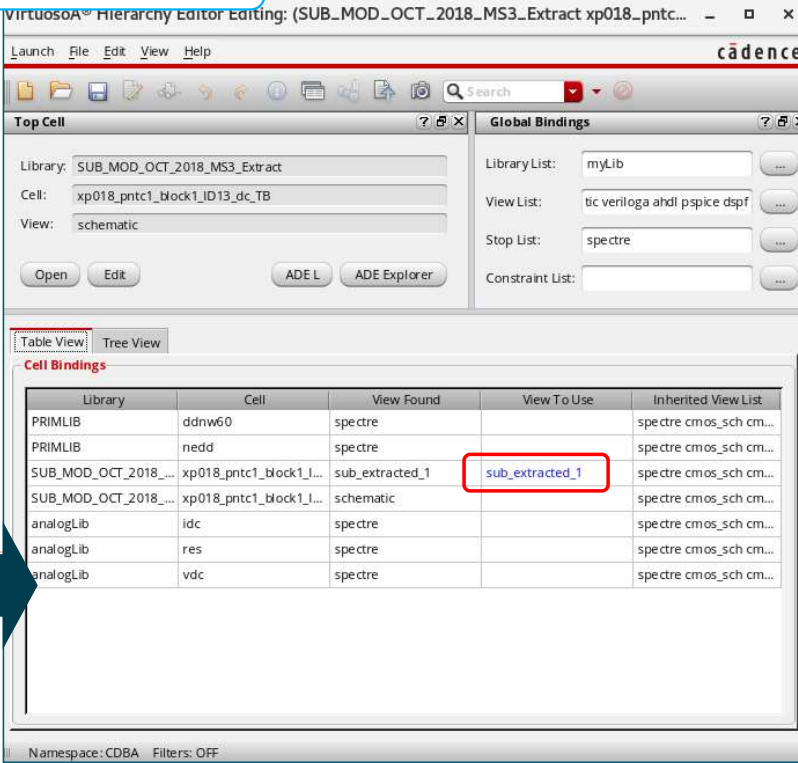
PNAware RC: How to use it?

- > To run PNAwareRC: 1. LVS clean design. 2. Add recognition layer SUBEXT in layout over regions of interest

GUI



Simulation



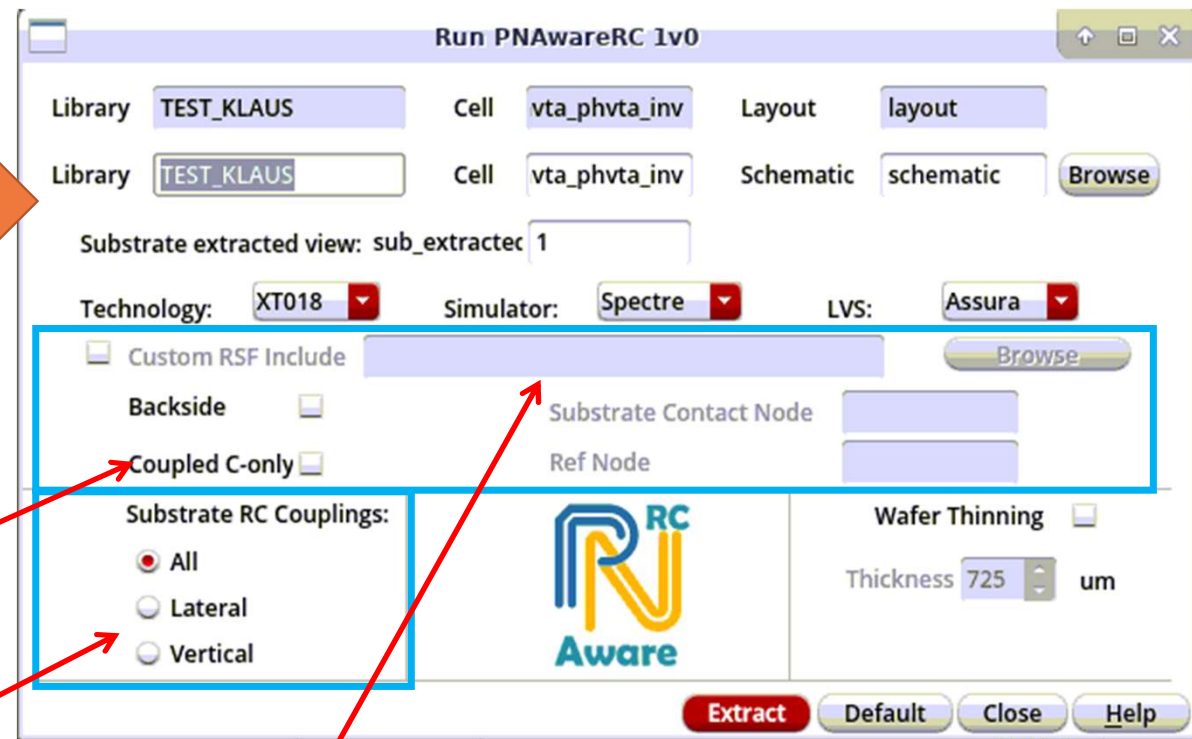
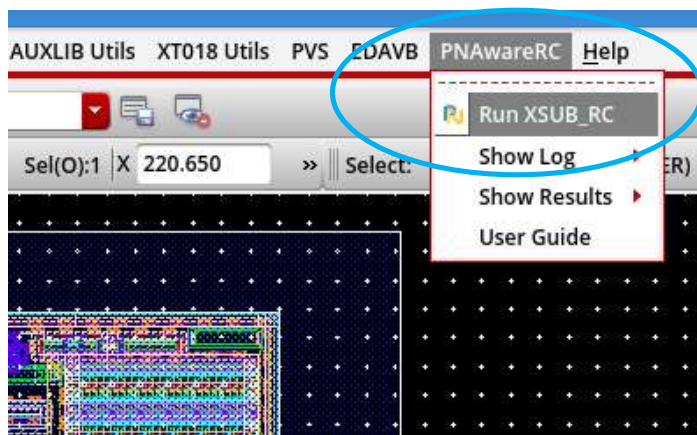
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```

PNAwareRC: useful extraction options

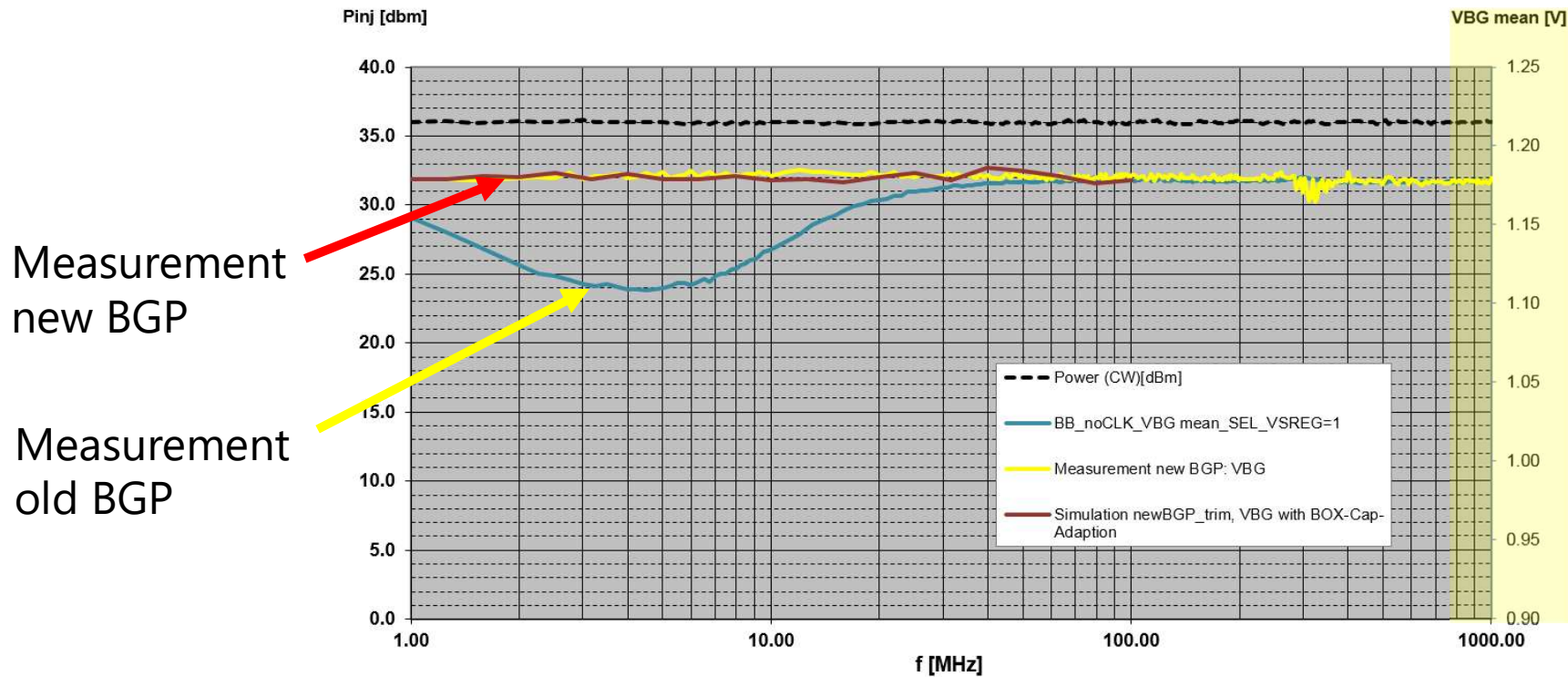
➤ Launch PNAwareRC -> Run XSUB_RC



- Backside contact
- Wafer thinning
- **include parasitic metal caps (Coupled C-only)**
- **RC Coupling modes**
- **Customer specific RSF include file (if LVS switches are needed to get a clean LVS)**

Simulation results vs. measurement (bandgap voltage) –new BGP

- Re-design: Shielding of Diff-Pair by GND connection of substrate and other topology changes
- Good fit of measurement and simulation



Picture taken from X-FAB Technology Conference 2022, Dirk Nuernbergk

✓ PNAware - PNAwareRC: reduce the risk of re-designs

- ✓ Post-layout parasitic extraction Tools → post-layout substrate netlist including all relevant active and passive elements in the substrate
- ✓ Enable designers
 - to evaluate substrate problems by means of circuit simulation
 - to assess potential substrate coupling problems before the 1st Tape-Out
 - to evaluate circuit and guarding concepts with better immunity to substrate coupling

PNAware XSUB and PNAware RC: Integration in XFAB PDKs



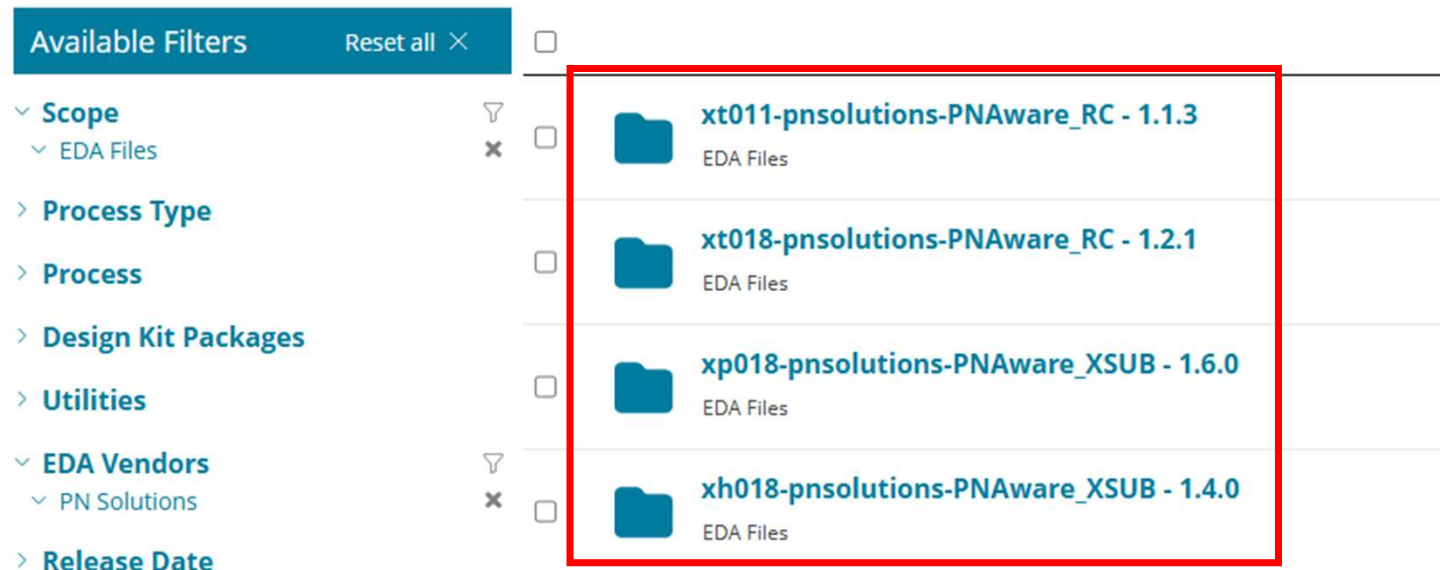
> PNAware XSUB available for HV-CMOS:

- XH018 Cadence PDK
- XP018 Cadence PDK



> PNAware RC available for SOI:

- XT018 Cadence PDK
- XT011 Cadence PDK





Everything
you need
to achieve
first-time-
right



xfab

Thank you